Preferred Device

General Purpose Transistor

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-723 package which is designed for low power surface mount applications.

• This is a Pb-Free Device

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	45	V
Collector-Base Voltage	V _{CBO}	50	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current – Continuous	I _C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) T _A = 25°C Derated above 25°C	P _D	260 2.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	R _θ JA	480	°C/W
Total Device Dissipation, FR-4 Board (Note 2) T _A = 25°C Derated above 25°C	P _D	600 4.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	205	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

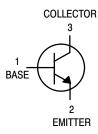
1. FR-4 @ Minimum Pad

- 2. FR-4 @ 1.0 × 1.0 Inch Pad



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http://onsemi.com





1F = Device Code

M = Date Code

MARKING

ORDERING INFORMATION

Device	Package	Shipping [†]		
BC847BM3T5G	SOT-723	8000/Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	I .
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	V _{(BR)CEO}	45	_	-	V
Collector – Emitter Breakdown Voltage $(I_C = 10 \mu A, V_{EB} = 0)$	V _{(BR)CES}	50	_	-	V
Collector – Base Breakdown Voltage ($I_C = 10 \mu A$)	V _{(BR)CBO}	50	-	-	V
Emitter – Base Breakdown Voltage ($I_E = 1.0 \mu A$)	V _{(BR)EBO}	6.0	_	-	V
Collector Cutoff Current $(V_{CB} = 30 \text{ V})$ $(V_{CB} = 30 \text{ V}, T_{A} = 150^{\circ}\text{C})$	I _{CBO}	-	- -	15 5.0	nA μA
ON CHARACTERISTICS	•		•		•
DC Current Gain $ (I_C = 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ \text{V}) $ $ (I_C = 2.0 \ \text{mA}, \ V_{CE} = 5.0 \ \text{V}) $	h _{FE}	- 200	150 290	- 450	_
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$)	V _{CE(sat)}	-	- -	0.25 0.6	V
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)	V _{BE(sat)}	-	0.7 0.9	- -	V
Base – Emitter Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)	V _{BE(on)}	580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTERISTICS	•				
Current – Gain – Bandwidth Product ($I_C = 10$ mA, $V_{CE} = 5.0$ Vdc, $f = 100$ MHz)	f _T	100	_	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	_	4.5	pF
Noise Figure (I _C = 0.2 mA, V_{CE} = 5.0 Vdc, R_S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	_	_	10	dB

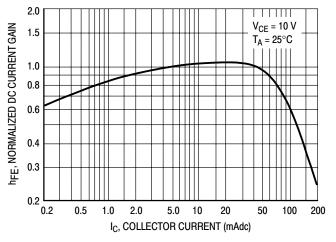


Figure 1. Normalized DC Current Gain

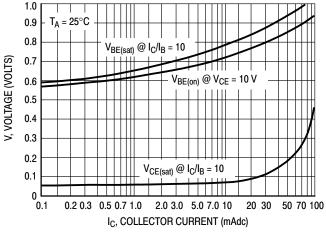


Figure 2. "Saturation" and "On" Voltages

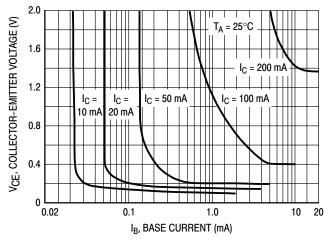


Figure 3. Collector Saturation Region

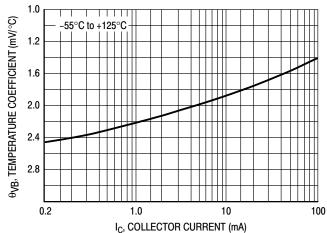
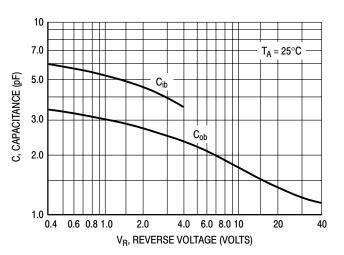


Figure 4. Base-Emitter Temperature Coefficient

BC847



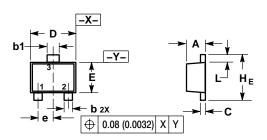
 f_{T} , CURRENT-GAIN – BANDWIDTH PRODUCT (MHz) 400 300 200 V_{CE} = 10 V T_A = 25°C 100 80 60 40 30 20 0.5 0.7 1.0 2.0 3.0 5.0 7.0 10 20 30 50 I_C, COLLECTOR CURRENT (mAdc)

Figure 5. Capacitances

Figure 6. Current-Gain - Bandwidth Product

PACKAGE DIMENSIONS

SOT-723 CASE 631AA-01 **ISSUE B**



STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

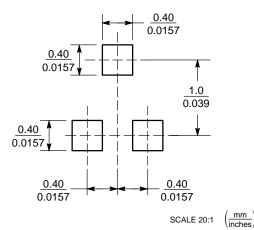
 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.21	0.27	0.0059	0.0083	0.0106
b1	0.25	0.31	0.37	0.010	0.012	0.015
С	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
Е	0.75	0.80	0.85	0.03	0.032	0.034
е	0.40 BSC			0.016 BSC		
ΗE	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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